Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1	(inorganic SiO SiN SiON) with between with (gate near oxide near (film layer)) with (gate near (insulat$3 dielectric) near (film layer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/08 08:48
L2	18	(inorganic SiO SiN SiON) same between same (gate near oxide near (film layer)) same (gate near (insulat$3 dielectric) near (film layer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/08 08:52
L3	1316	(inorganic SiO SiN SiON) and between and (gate near oxide near (film layer)) and (gate near (insulat$3 dielectric) near (film layer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/08 09:14
L4	6	3 and (organic adj ((thin adj film adj transistor$1) TFT$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/08 08:53
L5	10	3 and organic adj semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/08 09:36
L6	87	(inorganic near (material$1 layer film)) and between and (gate near oxide near (film layer)) and (gate near (insulat$3 dielectric) near (film layer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/08 09:36
L7	85190	(inorganic near (material$1 layer film))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/08 09:35
L8	904	7 and organic adj semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/08 09:36

L9	1	8 and (gate near oxide near (film layer)) with (gate near (insulat$3 dielectric) near (film layer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/08 09:37
L10	10	8 and (gate near oxide near (film layer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/08 09:37